

#### **Features**

- High Density Cell Design for Ultra Low R<sub>DS(on)</sub>
- · Fully Characterized Avalanche Voltage and Current
- · Excellent Package for Good Heat Dissipation
- · Epoxy Meets UL 94 V-0 Flammability Rating
- Moisture Sensitivity Level 3
- Halogen Free. "Green" Device (Note 1)
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

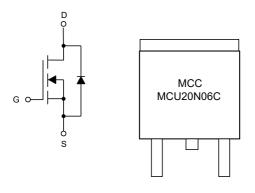
# **Maximum Ratings**

- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 1.05°C/W Junction to Case

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	60	V
Gate-Source Volltage	$V_{GS}$	±20	V
Continuous Drain Current	I <sub>D</sub>	20	Α
Pulsed Drain Current	I <sub>DM</sub>	62	Α
Single Pulse Avalanche Energy (Note 2)	E <sub>AS</sub>	24	mJ
Total Power Dissipation	P <sub>D</sub>	119	W

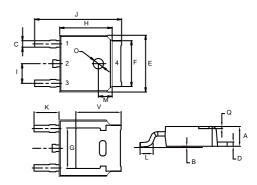
Note: 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds. 2.Vpp=50V, L=0.5mH,Rg=25Ω,las=9.8A,Starting T<sub>J</sub>=25°C.

# **Internal Structure and Marking Code**



# N-CHANNEL MOSFET

# **DPAK(TO-252)**



- 1. Gate
- 2,4. Drain
  - 3. Source

DIMENSIONS					
DIM	INCHES		MM		NOTE
DIIVI	MIN	MAX	MIN	MAX	NOTE
Α	0.087	0.094	2.20	2.40	
В	0.000	0.005	0.00	0.13	
С	0.026	0.034	0.66	0.86	
D	0.018	0.023	0.46	0.58	
E	0.256	0.264	6.50	6.70	
F	0.201	0.215	5.10	5.46	
G	0.190		4.83		TYP.
Н	0.236	0.244	6.00	6.20	
ı	0.086	0.094	2.18	2.39	
J	0.386	0.409	9.80	10.40	
K	0.1	14	2.9	90	TYP.
L	0.055	0.067	1.40	1.70	
M	0.063		1.6	60	TYP.
0	0.043	0.051	1.10	1.30	
Q	0.000	0.012	0.00	0.30	
V	V 0.211		5.3	35	TYP.



# Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	60			V
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			1	μA
Gate-Threshold Voltage <sup>(Note 3)</sup>	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0	1.56	2.5	V
(Alata 2)	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =10A		27 37		
Drain-Source On-Resistance <sup>(Note 3)</sup>		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A		34	48	mΩ
Dynamic Characteristics (Note 4)						
Input Capacitance	C <sub>iss</sub>			850		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =25V,V <sub>GS</sub> =0V,f=1MHz		53		
Reverse Transfer Capacitance	C <sub>rss</sub>			42		
Total Gate Charge	$Q_g$			20.62		nC
Gate-Source Charge	$Q_{gs}$	V <sub>DD</sub> =30V,V <sub>GS</sub> =10V,I <sub>D</sub> =10A		4.44		
Gate-Drain Charge	$Q_{gd}$			4.02		
Turn-On Delay Time	t <sub>d(on)</sub>			6.2		
Turn-On Rise Time	t <sub>r</sub>	V <sub>DD</sub> =30V, I <sub>D</sub> =10A,		26.2		no
Turn-Off Delay Time	t <sub>d(off)</sub>	$R_{G}=3\Omega$ , $V_{GS}=10V$		17		- ns
Turn-Off Fall Time	t <sub>f</sub>			30		
Drain-Source Body Diode Cha	racteristics	,		•		
Continuous Body Diode Current	Is				20	Δ.
Pulsed Diode Forward Current	I <sub>SM</sub>				62	Α
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> =10A, V <sub>GS</sub> =0V		0.88	1.2	V
Reverse Recovery Time	t <sub>rr</sub>	- V <sub>GS</sub> =0V, I <sub>F</sub> =10A,di/dt=100A/μs		26		ns
Reverse Recovery Charge	Q <sub>rr</sub>			3.2		nC

Note 3. Pulse Test : Pulse Width  $\leq\!300\mu s,$  Duty Cycle  $\leq\!2\%.$ 

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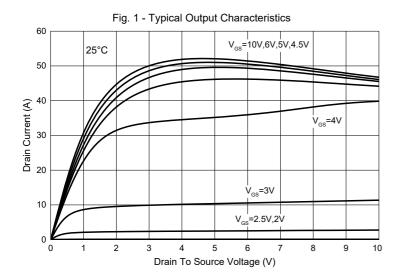
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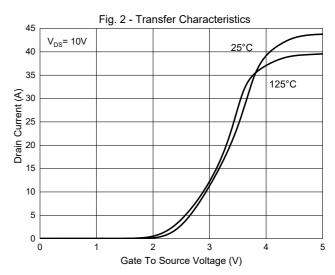
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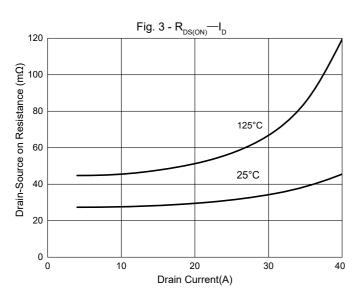
<sup>4.</sup> Guaranteed by Design, Not Subject to Production Testing.

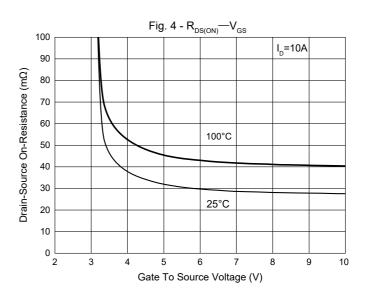


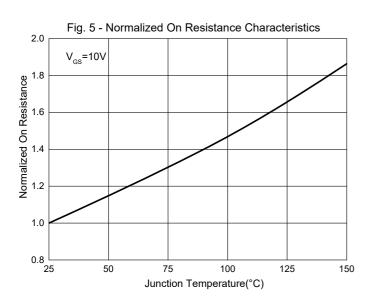
#### **Curve Characteristics**

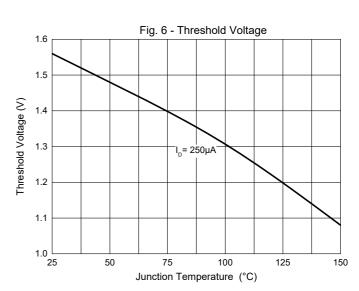






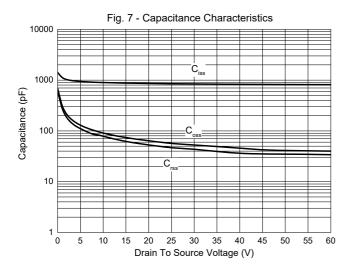


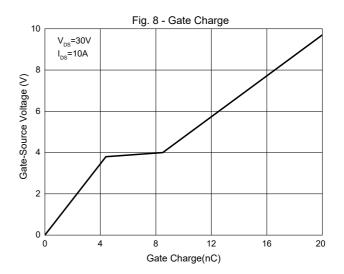


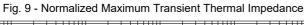


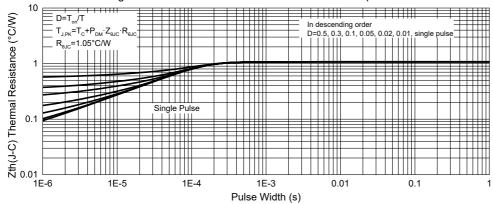


## **Curve Characteristics**











# **Ordering Information**

Device	Packing
Part Number-TP	Tape&Reel: 2.5Kpcs/Reel

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